# Quad 2-Input Data Selectors / Multiplexers

# **High-Performance Silicon-Gate CMOS**

The MC74HC157A is identical in pinout to the LS157. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device routes 2 nibbles (A or B) to a single port (Y) as determined by the Select input. The data is presented at the outputs in noninverted form. A high level on the Output Enable input sets all four Y outputs to a low level.

#### **Features**

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 82 FETs or 20.5 Equivalent Gates
- Pb-Free Packages are Available\*



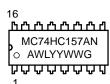
# ON Semiconductor®

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## MARKING DIAGRAMS

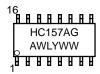


PDIP-16 N SUFFIX CASE 648





SOIC-16 D SUFFIX CASE 751B





TSSOP-16 DT SUFFIX CASE 948F





SOEIAJ-16 F SUFFIX CASE 966



A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week G = Pb-Free Package ■ = Pb-Free Package

(Note: Microdot may be in either location)

## ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

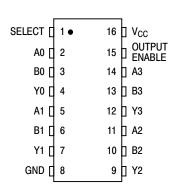


Figure 1. Pin Assignment

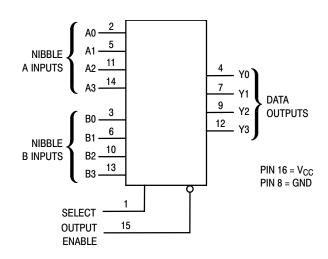


Figure 2. Logic Diagram

## **FUNCTION TABLE**

Inp		
Output Enable	Select	Outputs Y0 – Y3
Н	Х	L
L	L	A0-A3
L	Н	B0-B3

X = don't care A0 - A3, B0 - B3 = the levels of the respective Data-Word Inputs.

# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74HC157AN	PDIP-16	500 Units / Rail
MC74HC157ANG	PDIP-16 (Pb-Free)	500 Units / Rail
MC74HC157AD	SOIC-16	48 Units / Rail
MC74HC157ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74HC157ADR2	SOIC-16	2500 Units / Reel
MC74HC157ADR2G	SOIC-16 (Pb-Free)	2500 Units / Reel
MC74HC157ADTR2	TSSOP-16*	2500 Units / Reel
MC74HC157ADTR2G	TSSOP-16*	2500 Units / Reel
MC74HC157AFEL	SOEIAJ-16	2000 Units / Reel
MC74HC157AFELG	SOEIAJ-16 (Pb-Free)	2000 Units / Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. \*This package is inherently Pb–Free.

#### **MAXIMUM RATINGS**

	_		
Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	$-0.5$ to $V_{CC} + 0.5$	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	$-0.5$ to $V_{CC} + 0.5$	V
I <sub>in</sub>	DC Input Current, per Pin	± 20	mA
I <sub>out</sub>	DC Output Current, per Pin	± 25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	± 50	mA
P <sub>D</sub>	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

SOIC Package: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

## **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit	
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)		2.0	6.0	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)		0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Packa	ige Types	- 55	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (Figure 1)	$V_{CC} = 2.0 \text{ V}$ $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 0 0	1000 500 400	ns

# DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Test Conditions	V <sub>CC</sub>	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage	$V_{out} = V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V <sub>IL</sub>	Maximum Low–Level Input Voltage	$V_{out} = 0.1 \text{ V}$ $ I_{out}  \le 20  \mu\text{A}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	<b>&gt;</b>
V <sub>OH</sub>	Minimum High-Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out}  \le 20 \mu A$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	<b>&gt;</b>
		$\label{eq:Vin} \begin{array}{ll} V_{in} = V_{IH} &  I_{out}  \leq 2.4 \text{ mA} \\  I_{out}  \leq 6.0 \text{ mA} \\  I_{out}  \leq 7.8 \text{ mA} \end{array}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.2 3.7 5.2	

## DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guaranteed Limit		mit	
Symbol	Parameter	Test Conditions	v <sub>cc</sub> v	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
V <sub>OL</sub>	Maximum Low–Level Output Voltage	$V_{in} = V_{IL}$ $ I_{out}  \le 20 \mu A$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\begin{split} V_{in} = V_{IL} &  I_{out}  \leq 2.4 \text{ mA} \\  I_{out}  \leq 6.0 \text{ mA} \\  I_{out}  \leq 7.8 \text{ mA} \end{split}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.4 0.4 0.4	
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
I <sub>OZ</sub>	Maximum Three–State Leakage Current	Output in High-Impedance State $V_{in} = V_{IL}$ or $V_{IH}$ $V_{out} = V_{CC}$ or GND	6.0	± 0.5	± 5.0	± 10	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4.0	40	160	μΑ

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

# AC ELECTRICAL CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 6.0 \text{ ns}$ )

			Guaranteed Limit			
Symbol	Parameter	V <sub>CC</sub>	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A or B to Output Y (Figures 1 and 4)	2.0 3.0 4.5 6.0	105 65 21 18	130 85 26 22	160 115 32 27	ns
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Select to Output Y (Figures 2 and 4)	2.0 3.0 4.5 6.0	110 70 22 19	140 90 28 24	165 115 33 28	ns
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Output Enable to Output Y (Figures 3 and 4)	2.0 3.0 4.5 6.0	100 60 20 17	125 80 25 21	150 110 30 26	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 1 and 4)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 16	110 36 22 19	ns
C <sub>in</sub>	Maximum Input Capacitance	_	10	10	10	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
$C_{PD}$	Power Dissipation Capacitance (Per Package)*	33	pF

<sup>\*</sup> Used to determine the no–load dynamic power consumption:  $P_D = C_{PD} \ V_{CC}^2 f + I_{CC} \ V_{CC}$ . For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

#### PIN DESCRIPTIONS

## **INPUTS**

#### A0, A1, A2, A3 (Pins 2, 5, 11, 14)

Nibble A inputs. The data present on these pins is transferred to the outputs when the Select input is at a low level and the Output Enable input is at a low level. The data is presented to the outputs in noninverted form.

#### B0, B1, B2, B3 (Pins 3, 6, 10, 13)

Nibble B inputs. The data present on these pins is transferred to the outputs when the Select input is at a high level and the Output Enable input is at a low level. The data is presented to the outputs in noninverted form.

## **OUTPUTS**

## Y0, Y1, Y2, Y3 (Pins 4, 7, 9, 12)

Data outputs. The selected input Nibble is presented at these outputs when the Output Enable input is at a low level.

The data present on these pins is in its noninverted form. For the Output Enable input at a high level, the outputs are at a low level.

# CONTROL INPUTS Select (Pin 1)

Nibble select. This input determines the data word to be transferred to the outputs. A low level on this input selects the A inputs and a high level selects the B inputs.

## **Output Enable (Pin 15)**

Output Enable input. A low level on this input allows the selected input data to be presented at the outputs. A high level on this input sets all outputs to a low level.

#### **SWITCHING WAVEFORMS**

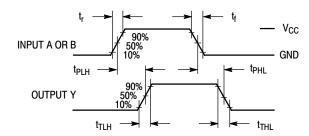


Figure 3. HC157A

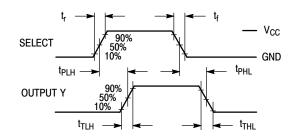


Figure 4. Y versus Selected, Noninverted

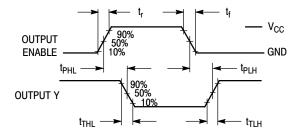
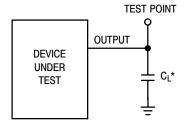


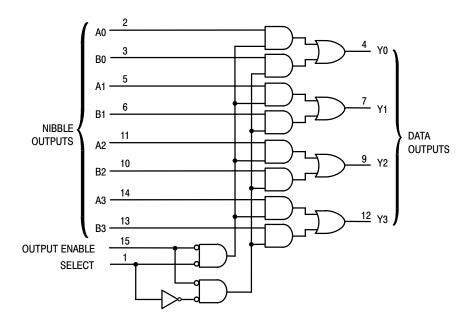
Figure 5. HC157A



\*Includes all probe and jig capacitance

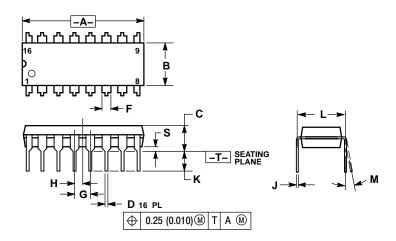
Figure 6. Test Circuit

# **EXPANDED LOGIC DIAGRAM**



#### **PACKAGE DIMENSIONS**

# PDIP-16 **N SUFFIX** CASE 648-08 **ISSUE T**

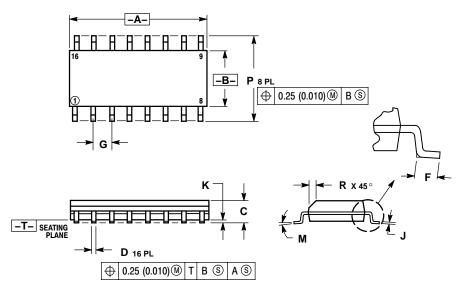


#### NOTES:

- DIMENSIONING AND TOLERANCING PER
- DIMENSIONING AND TOLERANCING F ANSI 714.5M, 1982.
   CONTROLLING DIMENSION: INCH.
   DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
   DIMENSION B DOES NOT INCLUDE MOLD FLASH.
- 5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.740	0.770	18.80	19.55
В	0.250	0.270	6.35	6.85
С	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100	BSC	2.54	BSC
Н	0.050	BSC	1.27	BSC
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0°	10 °	0°	10 °
S	0.020	0.040	0.51	1.01

# SOIC-16 **D SUFFIX** CASE 751B-05 **ISSUE J**



- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

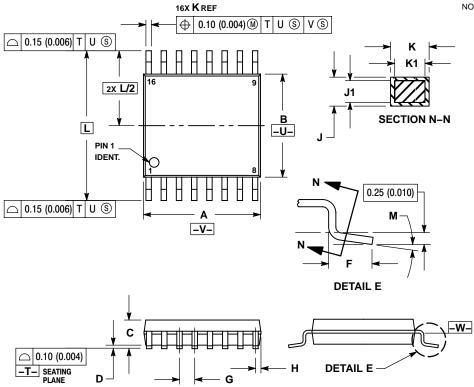
  4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIGN.

- MAXIMUM MOLD PHOLICISION 0.15 (0.006)
  PER SIDE.
  DIMENSION D DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR
  PROTRUSION SHALL BE 0.127 (0.005) TOTAL
  IN EXCESS OF THE D DIMENSION AT
  MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7°	0 °	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

#### **PACKAGE DIMENSIONS**

# TSSOP-16 **DT SUFFIX** CASE 948F-01 **ISSUE A**



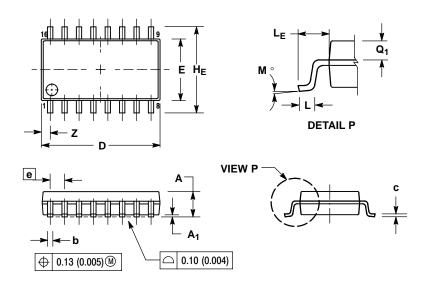
- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
  - 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
    2. CONTROLLING DIMENSION: MILLIMETER.
    3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
    4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
    5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K

  - (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL
  - 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
    7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
C		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026	BSC
Н	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8 °

# **PACKAGE DIMENSIONS**

SOEIAJ-16 **F SUFFIX** CASE 966-01 **ISSUE O** 



#### NOTES:

- 11ES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (6 006) PER SIDE.
- OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

  4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

  5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
þ	0.35	0.50	0.014	0.020
C	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
Ε	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050	BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10 °	0°	10°
Q	0.70	0.90	0.028	0.035
Z		0.78		0.031

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